L Number	Hits	Search Text	DB	Time stamp
1	891	((CMOS or MOS) with transistor) and (bipolar with transistor) and (BOX or	USPAT; EPO; JPO;	2004/10/04 09:03
2	67	(buried adj oxide) or (buried adj insulat\$4)) (((CMOS or MOS) with transistor) and (bipolar with transistor) and (BOX or (buried adj oxide) or (buried adj insulat\$4))) and ((single adj	DERWENT; IBM_TDB USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/10/04 09:32
3	67	crystalline) with semiconductor)	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/10/04 09:04
4 .	52	substrate ((((CMOS or MOS) with transistor) and (bipolar with transistor) and (BOX or (buried adj oxide) or (buried adj insulat\$4))) and ((single adj crystalline) with semiconductor)) and	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/10/04 09:04
5	25	(bipolar with substrate) ("4008111" "4571818" "4601779" "4649627" "4893509" "4910165" "4985745" "5004705" "5086011" "5143862" "5234535" "5258318" "5294823" "5321298" "5352912" "5481126" "5496745" "5516718" "5543653" "5627092" "5656514" "5770484" "5789793" "5895953" "5956597").PN.	USPAT	2004/10/04 09:17
6	4	· ·	USPAT	2004/10/04
7	5	5573972.URPN.	USPAT	2004/10/04
8	159	SOI and bulk and ((single adj crystalline) with semiconductor)	USPAT; EPO; JPO; DERWENT; IBM TDB	2004/10/04 09:33
9	57	(SOI and bulk and ((single adj crystalline) with semiconductor)) and bipolar	USPAT; EPO; JPO; DERWENT; IBM TDB	2004/10/04 09:37
10	1792	257/347.ccls.	USPAT; EPO; JPO; DERWENT;	2004/10/04 09:50
11	391	257/349.ccls.	IBM_TDB USPAT; EPO; JPO; DERWENT;	2004/10/04 09:52
12	860	257/370.ccls.	IBM_TDB USPAT; EPO; JPO; DERWENT;	2004/10/04 10:12
13	668	257/378.ccls.	IBM_TDB USPAT; EPO; JPO; DERWENT;	2004/10/04 10:12
-	2	("6724045").PN.	IBM_TDB USPAT; EPO; JPO; DERWENT;	2004/06/26
-	9	("5102809" "5212397" "5258318" "5294823" "5371401" "5430318" "5909626" "6096584" "6232649").PN.	IBM_TDB USPAT	2004/06/26 18:27
-	1897	bicmos.ab.	USPAT; EPO; JPO; DERWENT; IBM TDB	2004/06/26 18:49

	37	bicmos.ab. and MOS and bipolar and	USPAT;	2004/06/26
		(buried with insulat\$4)	EPO; JPO;	18:54
			DERWENT;	•
			IBM_TDB	
-	153	1 '	USPAT;	2004/06/26
		bipolar and (buried with insulat\$4)	EPO; JPO;	18:55
		·	DERWENT;	
_	96	((element adj isolation) and MOS and	IBM_TDB USPAT;	2004/06/26
]	bipolar and (buried with insulat\$4)) and	EPO; JPO;	19:03
		(bipolar adj transistor) and (MOS adj	DERWENT;	13.03
		transistor)	IBM TDB	
_	10	1	USPAT;	2004/06/26
		bipolar and (buried with insulat\$4)) and	EPO; JPO;	19:04
		((bipolar adj transistor) and (MOS adj	DERWENT;	
		transistor)).ab.	IBM_TDB	
-	5	("5356827" "5476809" "5529947"	USPAT	2004/06/26
		"5573972" "5688702").PN.		19:07
-	6	5688702.URPN.	USPAT	2004/06/26
	24	/!! 4120440!! !! 4467244!! !! 4507545!!		19:17
-	24	("4139442" "4467344" "4587545" "4602268" "4608590" "4754310"	USPAT	2004/06/26
		4802266		19:18
		"5181095" "5216275" "5336634"		
		"5466963" "5467347" "5479498"	<u> </u>	i i
· 1		"5512774" "5554872" "5683075"		
		"5688702" "5841197" "5856700"		
		"5872044" "5914280" "5939755").PN.		
-	5	CMOS and bipolar and (CMOS with (buried	USPAT;	2004/06/26
		adj insulat\$4)) and (CMOS and	EPO; JPO;	19:27
		bipolar).ab.	DERWENT;	
			IBM_TDB	
-	0	CMOS and bipolar and (CMOS with (buried	USPAT;	2004/06/26
		adj insulat\$4)) and (element adj	EPO; JPO;	19:28
		isolation)	DERWENT;	
_	347	CMOS and bipolar and (element adj	IBM_TDB USPAT;	2004/06/26
	34'	isolation)	EPO; JPO;	19:29
			DERWENT;	19.29
			IBM TDB	
_	70	(CMOS and bipolar and (element adj	USPAT;	2004/06/26
	· ·	isolation)) and (BOX or (buried adj	EPO; JPO;	19:30
		oxide) or (buried adj insulat\$4))	DERWENT;	
		-	IBM_TDB	
-	857	((CMOS or MOS) with transistor) and	USPĀT;	2004/10/04
		(bipolar with transistor) and (BOX or	EPO; JPO;	09:02
		(buried adj oxide) or (buried adj	DERWENT;	
I _	100	insulat\$4))	IBM_TDB	2004/05/25
] _	183	(((CMOS or MOS) with transistor) and (bipolar with transistor) and (BOX or	USPAT;	2004/06/26
		(buried adj oxide) or (buried adj	EPO; JPO; DERWENT;	19:31
		insulat\$4))) and bipolar.ab.	IBM TDB	
-	15	((((CMOS or MOS) with transistor) and	USPAT;	2004/06/26
		(bipolar with transistor) and (BOX or	EPO; JPO;	20:07
		(buried adj oxide) or (buried adj	DERWENT;	
		insulat\$4))) and bipolar.ab.) and	IBM TDB	
		(element adj isolation)	_	
-	191	(((CMOS or MOS) with transistor) and	USPAT;	2004/06/26
	[(bipolar with transistor) and (BOX or	EPO; JPO;	19:37
		(buried adj oxide) or (buried adj	DERWENT;	
]_	67	insulat\$4))) and bicmos	IBM_TDB	2004/06/26
-	"'	((((CMOS or MOS) with transistor) and (bipolar with transistor) and (BOX or	USPAT;	2004/06/26 19:38
		(buried adj oxide) or (buried adj	EPO; JPO; DERWENT;	15.30
		insulat\$4))) and bicmos) and ((element or	IBM TDB	
		trench) adj isolation)		
	8	("4038680" "4089021" "4780430"	USPAT	2004/06/26
		"5023194" "5065213" "5118635"		19:40
		"5344785" "5716887").PN.	l '	,
-	4	("5100810" "5102809" "5593915"	USPAT	2004/06/26
		"5952695").PN.		19:44

-	35	5100810.URPN.	USPAT	2004/06/26
-	22	("3913124" "4700461" "4769687" "4839309" "4884117" "4965872" "5028557" "5049513" "5057580"	USPAT	2004/06/26
		"5060035" "5072274" "5073506" "5075241" "5100810" "5102809"		
		"5140390" "5162882" "5212397" "5241211" "5273915" "5289027" "5621239").PN.		
-	35		USPAT	2004/06/26 19:58
-	975	((CMOS or MOS) with transistor) and ((bipolar or NPN or PNP) with transistor) and (BOX or (buried adj oxide) or (buried adj insulat\$4))	USPAT; EPO; JPO; DERWENT; IBM TDB	2004/06/26
-	131	(((CMOS or MOS) with transistor) and ((bipolar or NPN or PNP) with transistor) and (BOX or (buried adj oxide) or (buried adj insulat\$4))) and ((CMOS or MOS) with ((BOX or (buried adj oxide) or (buried adj insulat\$4))))	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/06/26
_	17	<pre>((((CMOS or MOS) with transistor) and ((bipolar or NPN or PNP) with transistor) and (BOX or (buried adj oxide) or (buried adj insulat\$4))) and ((CMOS or MOS) with ((BOX or (buried adj oxide) or (buried adj insulat\$4))))) and (element adj isolation)</pre>	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/06/26 20:07